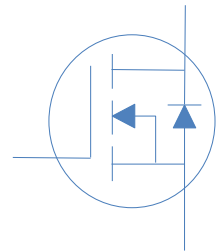


60V N-Ch Power MOSFET

V_{DS}		60	V
R	TO-263	1.45	m
R	TO-247	1.55	m
R	TO-220	1.67	m
I_D (Silicon Limited)		340	A
I_D (Package Limited)		120	A



Part Number	Package	Marking
HGB016N06S	TO-263	GB016N06S
HGK018N06S	TO-247	GK018N06S
HGP019N06S	TO-220	GP019N06S

Absolute Maximum Ratings at T_J

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	340	A
		T_C	240	
		T_C	120	
Continuous Drain Current (Package Limited)		T_C	120	
Drain to Source Voltage	V_{DS}	-	60	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	900	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.4mH, T_C$	720	mJ
	P_D	T_C	375	W
	T_J, T_{stg}	-	-55 to 175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	R	0.4	
Thermal Resistance Junction-Ambient	R	60	

Electrical Characteristics at T_j
Static Characteristics

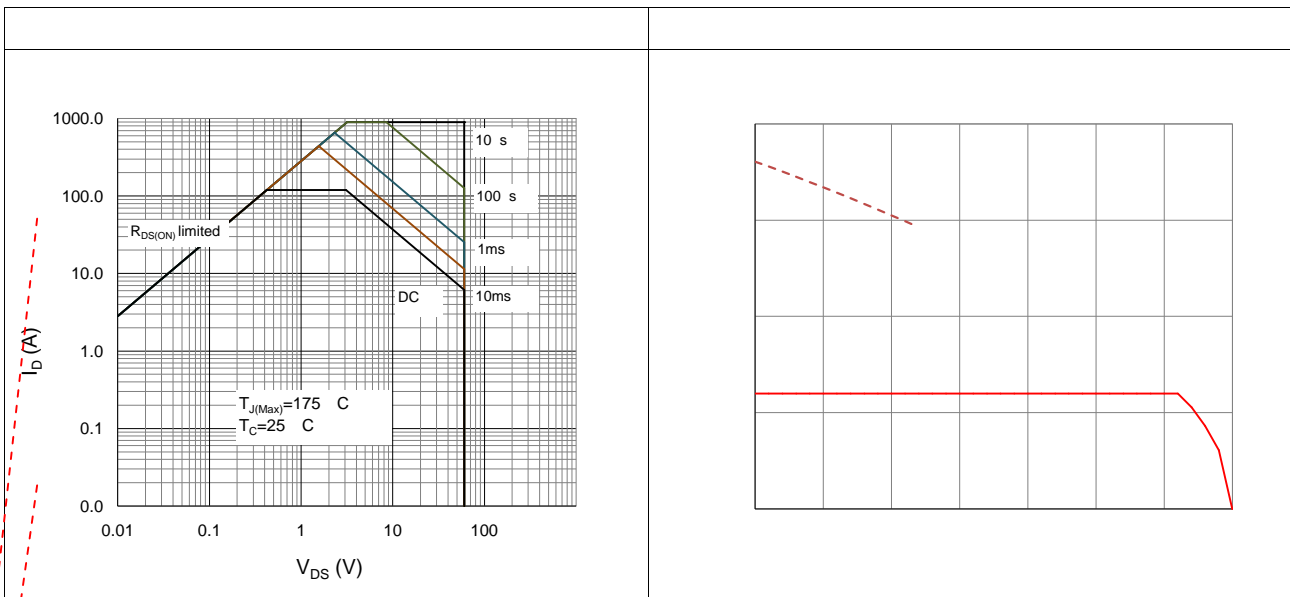
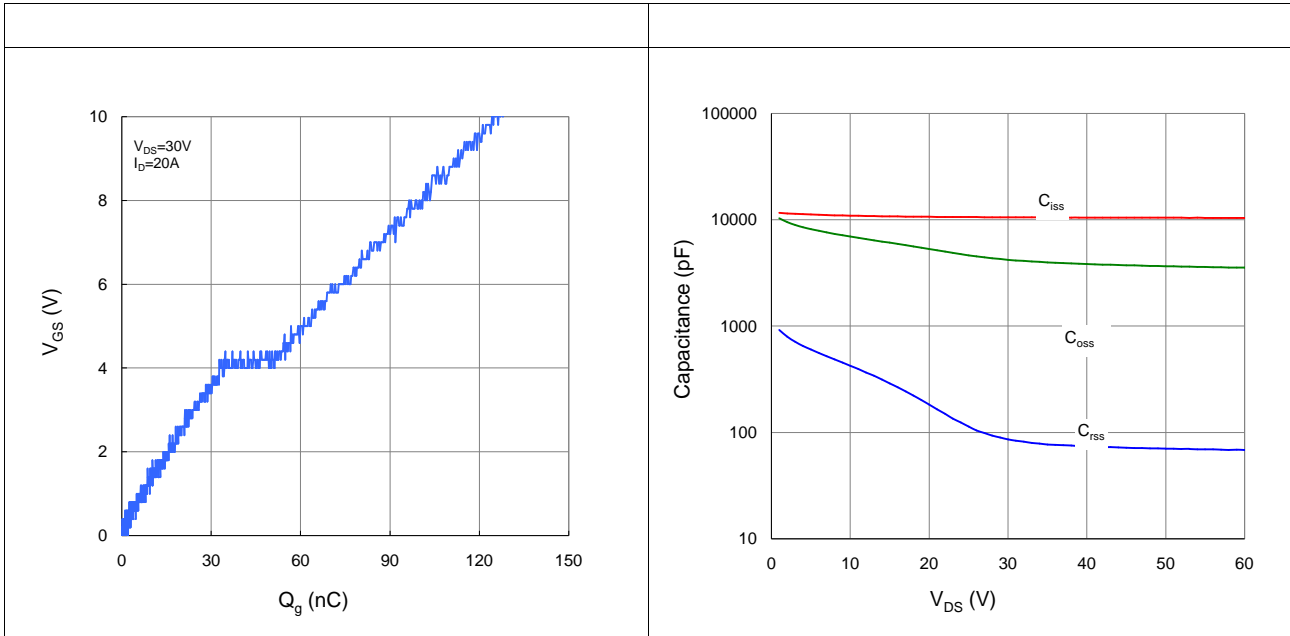
Parameter	Symbol	Conditions	Value			Unit	
			min		max		
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250 A$	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250 A$	2	3	4	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V, T_j$	-	-	1	A	
		$V_{GS}=0V, V_{DS}=60V, T_j$	-	-	100		
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA	
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	TO-263	-	1.45	1.6	m
			TO-247	-	1.55	1.8	
			TO-220	-	1.67	1.9	
Transconductance	g	$V_{DS}=5V, I_D=20A$	-	92	-	S	
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$	-	0.7	-		

Dynamic Characteristics

	C_{iss}	$V_{GS}=0V, V_{DS}$	-	10570	-	
	C_{oss}		-	4050	-	
	C_{rss}		-	84	-	
Total Gate Charge	Q_g	$V_{DD}=30V, I_D=20A, V_{GS}=10V$	-	124	-	nC
Gate to Source Charge	Q_{gs}		-	30	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	20	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=20A, V_{GS}=10V, R_G=3 \Omega$	-	35	-	ns
Rise time	t_r		-	27	-	
	t		-	70	-	
Fall Time	t		-	15	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=30V, I_F=20A, dl_F$	-	75	-	ns
Reverse Recovery Charge	Q_{rr}		s	-	260	-

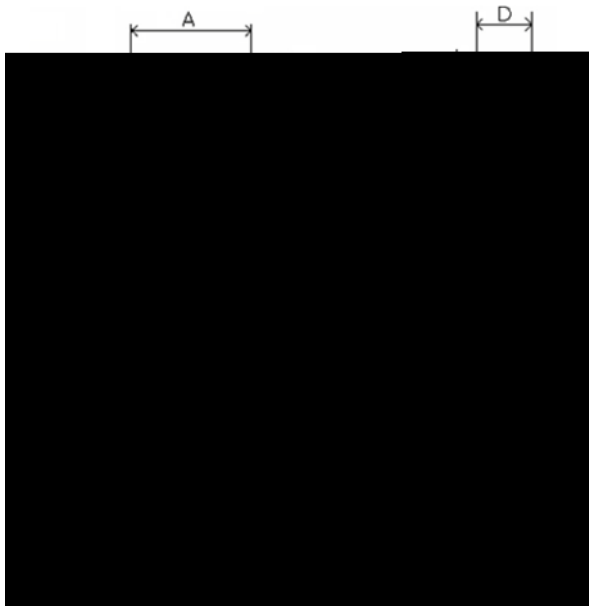


Inductive switching Test

Gate Charge Test

Diode Recovery Test

TO-220, 3 leads



Symbol	Min	Nom	Max
A	9.66	9.97	10.28
A2	9.80	10.00	10.20
B	15.60	15.70	15.80
C	12.70	13.48	14.27
D	4.30	4.50	4.70
E	9.00	9.20	9.40
F		2.54	
G1	1.32	1.52	1.72
G2	0.70	0.82	0.95
G3	0.45	0.52	0.60
H	3.50	3.60	3.70
I	2.70	2.80	2.90
J	15.70	15.97	16.25
K	2.20	2.40	2.60
L	1.15	1.27	1.40
N	6.40	6.60	6.80

TO-263, 2 leads

Symbol	Min	Nom	Max
A	9.66	9.97	10.28
B	1.02	1.17	1.32
C	8.59	9.00	9.40
D1	1.14	1.27	1.40
D2	0.70	0.83	0.95
D3		5.08	
E	15.09	15.24	15.39
F	1.15	1.28	1.40
G	4.30	4.50	4.70
H	2.29	2.54	2.79
I		0.25	
K	1.30	1.45	1.60
a1	0.45	0.55	0.65
a2(degree)	0°		8°

TO-247, 3 leads

